

00/505219  
DT09 Rec'd PCT/PTO 20 AUG 2004

INFORMATION DISCLOSURE STATEMENT PTO-1449	Attv. Docket No. 042112	Serial No. <del>New Admin.</del> 10/505,219
	Applicant(s): Hideo HOSONO et al.	
	Filing Date: August 20, 2004	Group Art Unit: 2891

### FOREIGN PATENT DOCUMENTS

Document No.						Date	Country	Translation (Yes or No)
<u>/MWS/</u>	AA	2002-80222	03/19/02	Japan	Abstract & Cited in Int'l Search Rep.			

### OTHER DOCUMENTS

/MWS/	AB	Hidenori HIRAMATSU et al., "Wide-gap p-gata Handotai LaCuOS no Epitaxial Seicho to Kobutsusei", Dai 49 Kai Oyo Butsurigaku Kankei Rengo Koenkai Koen Yokoshu, 27 March, 2002 No. 2, page 629. Cited in the PCT search report.
/MWS/	AC	K. UEDA et al., "Room temperature exciton in wide-gaps layered-oxysulfide semiconductor: LaCuOS", Applied Physics Science, 16 April 2001 Vol. 78, No. 16 pp.2333-2335. Cited in the PCT search report.
/MWS/	AD	K. UEDA et al., "Transparent p-type semiconductor: LaCuOS layered oxysulfide", App. Phys. Letter, 23 October, 2000, Vol. 77, No. 17, pp. 2701 to 2703. Cited in the PCT search report.
/MWS/	AE	D.O. Charkin et al., Russian Journal of Inorganic Chemistry, Vol. 44, No. 6, 1999, pp. 833-837
/MWS/	AF	Kenji ISHIKAWA et al., J. Electrochem. Soc., Vol. 138, No. 4, April 1991, pp. 1166-1170
/MWS/	AG	Yoshiki TAKANO et al., ELSEVIER, Physica B 206 & 207 (1995) pp. 764-766
/MWS/	AH	Hidenori HIRAMATSU et al., Journal of Applied Physics, Vol. 91, No. 11, 1 June 2002, pp. 9177-9181
/MWS/	AI	Kazushige UEDA et al., ELSEVIER, The Solid Films 411 (2002) pp. 115-118
/MWS/	AJ	Kazushige UEDA et al., Journal of Applied Physics, Vol. 91, No. 7, 1 April 2002 pp. 4768-4770

Examiner

/Matthew Such/

Date Considered

06/12/2007